FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Attorney Docket No.: A5771/T42200	Application No.: 09/854,083
	Applicant: ZHENGQUAN TAN et al.	
	Filing Date: May 11, 2001	Group: ~~Unassigned~~ 2823

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Reference Designation — **U.S. PATENT DOCUMENTS** —

Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)
AA	4,667,365	05/26/87	Martinek	16	35 D	
AB	4,894,352	01/16/90	Lane et al.	437	238	
AC	5,013,691	05/07/91	Lory et al.	437	238	
AD	5,571,571	11/05/96	Musaka et al.	427	574	
AE	5,571,576	11/05/96	Qian et al.	427	574	
AF	5,728,621	03/17/98	Zheng et al.	438	427	
AG	5,750,211	05/12/98	Weise et al.	427	579	
AH	5,872,058	02/16/99	Van Cleemput et al.	438	692	
AI	6,020,458	02/01/00	Lee et al.	528	401	
AJ	6,051,321	04/18/00	Lee et al.	428	447	
AK	6,149,779	11/21/00	Van Cleemput	204	192.37	
AL	6,150,212	11/21/00	Divakaruni et al.	438	244	
AM	6,150,285	11/21/00	Besser et al.	438	787	
AN	6,194,038	02/27/01	Rossman	427	569	
AO	6,197,691	03/06/01	Lee	438	691	

FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Class	Sub-class	Translation (Yes/No)
AP	EP 0 822 585 A2	02/04/98	Europe	H01L	21/316	yes

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

AQ	V.Y. Vassiliev et al., "Trends in Void Free Pre-metal CVD Dielectrics," *Solid State Technology*, pp. 129-136 (March 2001).
AR	L.Q. Qian et al., "High Density Plasma Deposition and Deep Submicron Gap Fill with Low Dielectric Constant SiOF Films," *February 21-22, 1995 DUMIC Conference*, pp. 50-56 (February 1995).
AS	T. Fukada et al., "Preparation of SiOF with Low Dielectric Constant by ECR Plasma CVD," *February 21-22, 1995 DUMIC Conference*, pp. 43-49 (February 1995).
AT	D. Yu et al., "Step Coverage Study of PETEOS Deposition for Intermetal Dielectric Applications," *June 12-13, 1990 VMIC Conference*, pp. 166-172 (June 1990).
AU	K. Musaka et al., "Single Step Gap Filling Technology for Subhalf Micron Metal Spacings on Plasma Enhanced TEOS/O_2 Chemical Vapor Deposition System," *Extended Abstracts of the 1993 International Conference on Solid State Devices and Materials, Makuhari*, pp. 510-512 (1993).
AV	T. Fukuda et al., "Highly Reliable SiOF Film Formation Using High Density Plasma Containing Hydrogen," *February ~~10-11~~, 1997 DUMIC Conference*, pp. 41-49 (February 1997).

EXAMINER William D. Coleman DATE CONSIDERED April 12, 2002

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.